

BRBS08065RA

Rev.A Apr.-2024

描述 / Descriptions

TO-220 塑封封装 单向可控硅。

Thyristor in a TO-220 Plastic Package.

特征 / Features

芯片采用玻璃钝化和塑氧环脂封装。

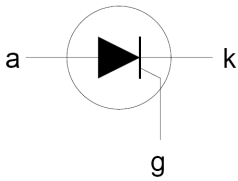
Glass passivated thyristors in a plastic envelope.

用途 / Applications

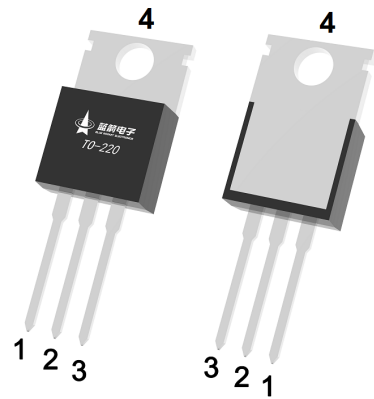
主要应用于要求双向高电压承受能力和高效热转换领域，其典型应用于马达控制、工业和家庭照明、加热和静电开关。

Use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Cathode PIN 2,4 : Anode PIN 3 : Gate

印章代码 / Marking

见印章说明。

See Marking Instructions.

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Repetitive peak off-state/reverse voltages(T _j =25°C)	V _{DRM} /V _{R_{RM}}	650	V
Average on-state current (T _c ≤105°C)	I _{T(AV)}	8	A
RMS on-state current(T _c =105°C)	I _{T(RMS)}	12	A
Non repetitive surge peak on-state current (tp=10ms, T _j =25°C)	I _{TSM}	120	A
Non repetitive surge peak on-state current (tp=8.3ms, T _j =25°C)		132	
Peak gate current(tp =20μs T _j =125°C)	I _{GM}	2.0	A
Average gate power dissipation(T _j =125°C)	P _{G(AV)}	0.5	W
Operating junction temperature range	T _j	-40~125	°C
Storage junction temperature range	T _{stg}	-40~150	°C
Junction to ambient(AC)	R _{th(j-a)}	60	°C/W
Junction to case for(AC)	R _{th(j-c)}	1.3	

电性能参数 / Electrical Characteristics(T_j=25°C)

符号 Symbol	测试条件 Test Conditions		数值 Value	单位 Unit	
I _{GT}	V _D =12V R _L =33Ω		Max.	15	mA
V _{GT}			Max.	1.0	V
V _{GD}	V _D =V _{DRM} T _j =125°C R _L =3.3KΩ		Min.	0.2	V
I _L	I _G =1.2I _{GT}		Max.	40	mA
I _H	I _T =100mA		Max.	30	mA
dV/dt	V _D =67% V _{DRM} Gate Open	T _j =125°C	Min.	200	V/μs
V _{TM}	I _{TM} =23A t _p =380μs	T _j =25°C	Max.	1.6	V
I _{DRM}	V _D =V _{DRM} V _R =V _{R_{RM}}	T _j =25°C		10	μA
I _{R_{RM}}		T _j =125°C		1	mA

电参数曲线图 / Electrical Characteristic Curve

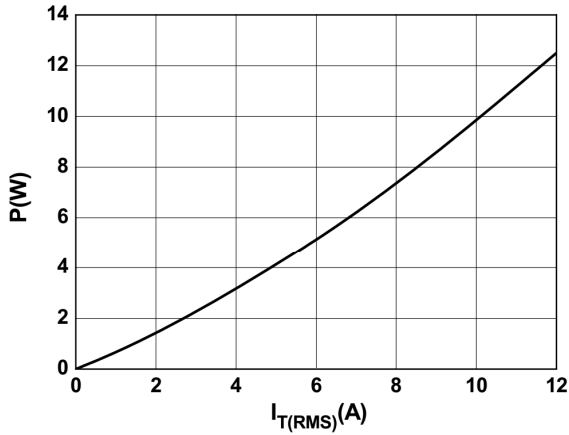


FIG.1 Maximum power dissipation versus RMS on-state current

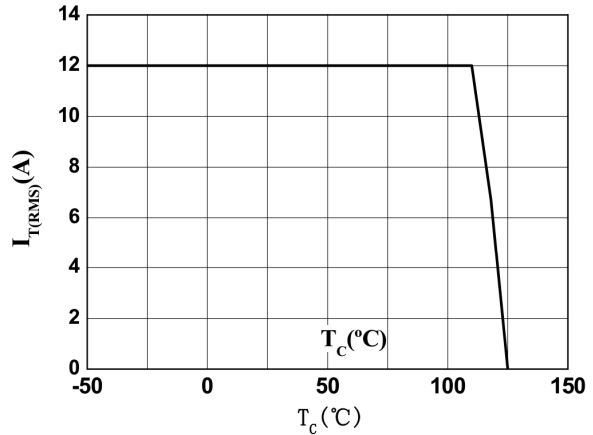


FIG.2: RMS on-state current versus case temperature

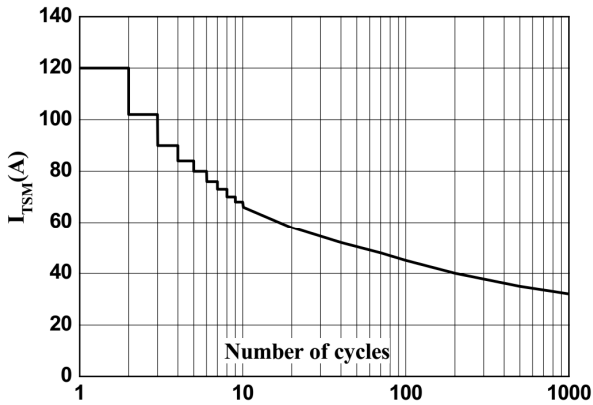


FIG.3: Surge peak on-state current versus number of cycles

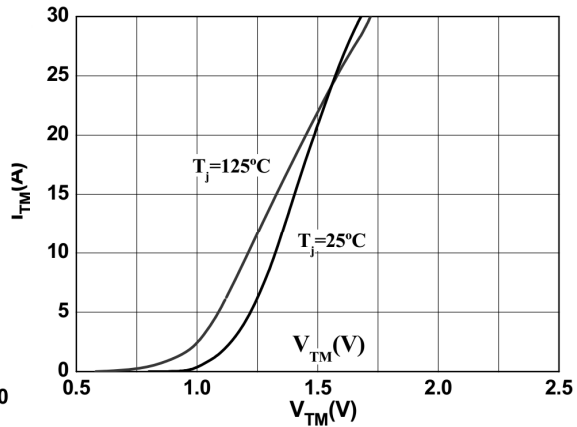


FIG.4: On-state characteristics

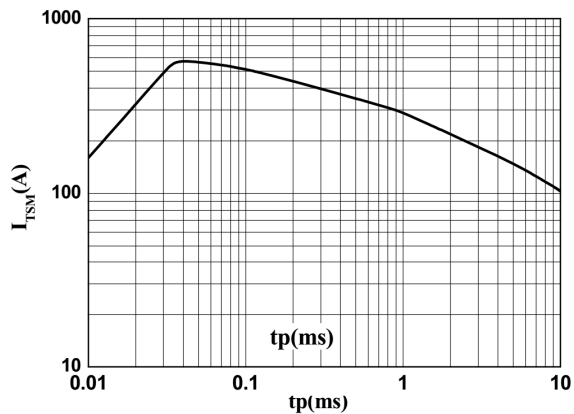


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20\text{ms}$, and corresponding value of I_2t ($dI/dt < 100\text{A}/\mu\text{s}$)

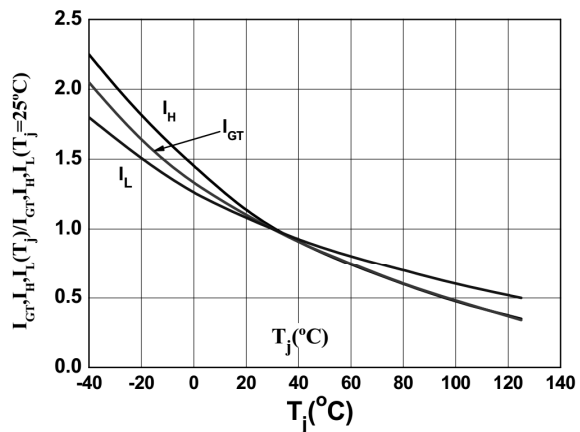
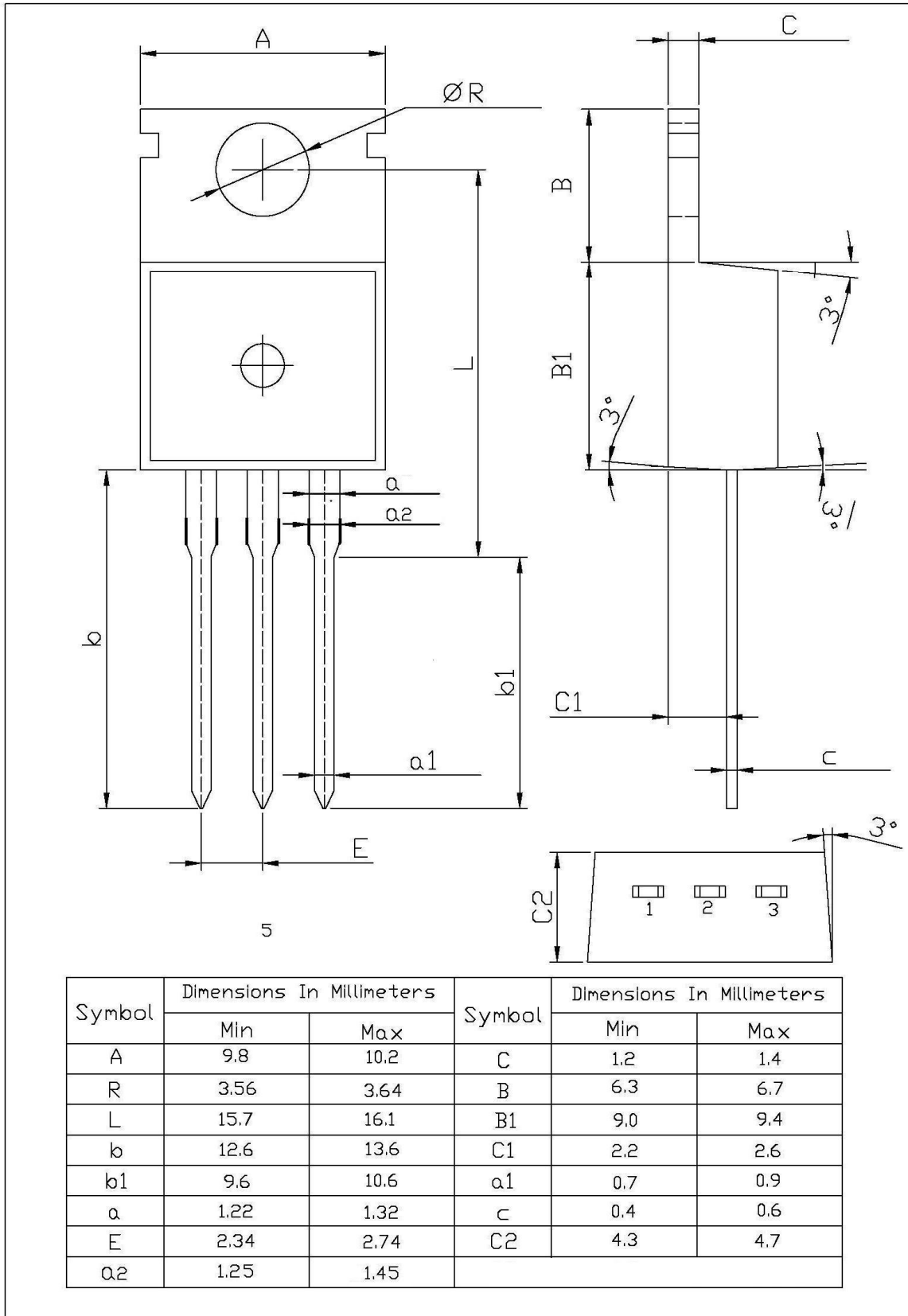


FIG.6: Relative variations of gate trigger current, holding current and latching current versus junction temperature

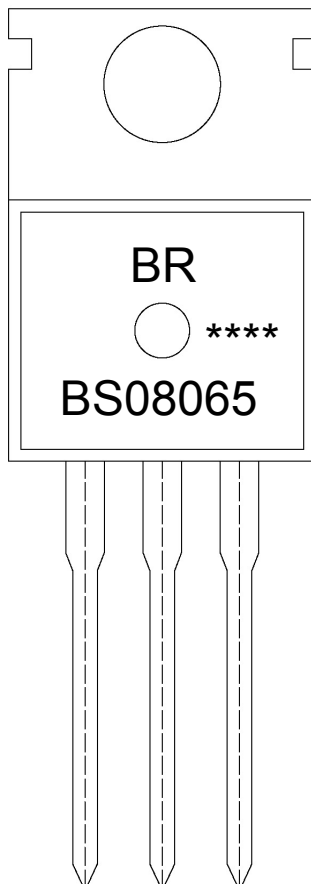
外形尺寸图 / Package Dimensions

T□-220

单位: mm



印章说明 / Marking Instructions



说明：

BR： 为公司代码

****： 为生产批号代码，随生产批号变化

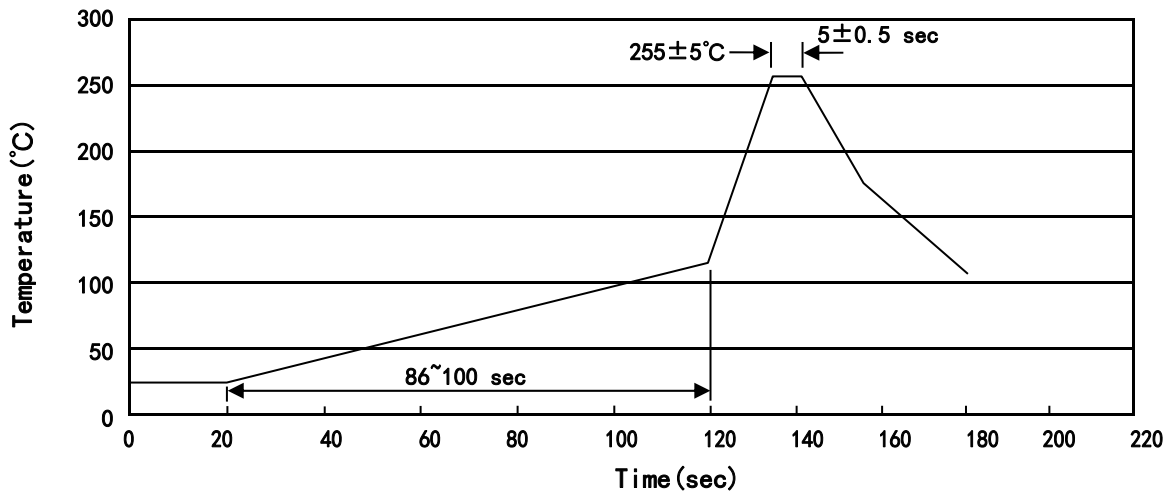
BS08065： 为型号代码

Note:

BR: Company Code

****: Lot No. Code, code change with Lot No

BS08065: Product Type Code

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)


说明：

- 1、预热温度 25~150°C，时间 60~90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices